

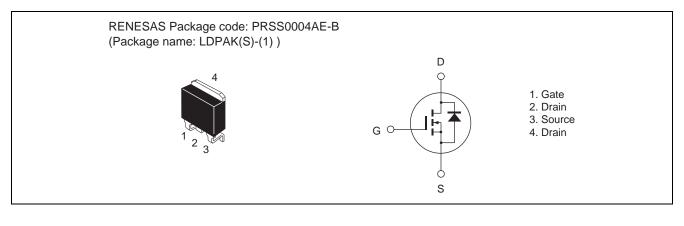
RJK5026DPE

Silicon N Channel MOS FET High Speed Power Switching

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

REJ03G1852-0100

Rev.1.00 Oct 26, 2009

ltem	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	6	А
Drain peak current	Note1 D (pulse)	18	А
Body-drain diode reverse drain current	I _{DR}	6	А
Body-drain diode reverse drain peak current	Note1 DR (pulse)	18	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch Note2	62.5	W
Channel to case thermal impedance	θch-c	2	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10~\mu s,~duty~cycle \leq 1\%$

2. Value at Tc = $25^{\circ}C$

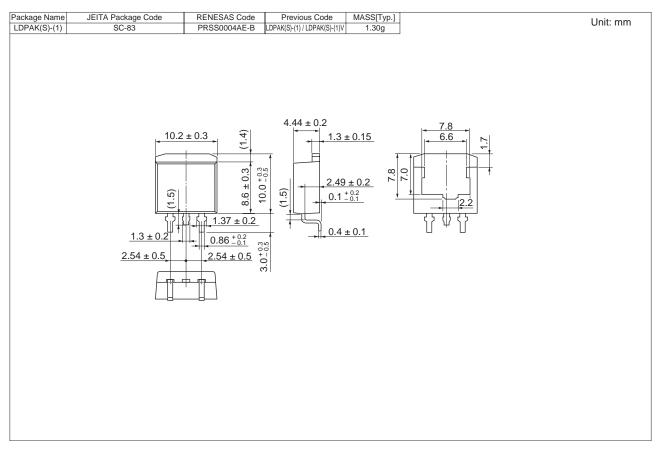
3. STch = 25°C, Tch \leq 150°C

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	1.35	1.70	Ω	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss	_	440		pF	V _{DS} = 25 V
Output capacitance	Coss	—	52		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		7		pF	
Turn-on delay time	t _{d(on)}	_	26	_	ns	I _D = 3 A
Rise time	tr	_	19	_	ns	$V_{GS} = 10 V R_L = 83.3 \Omega Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	50		ns	
Fall time	t _f	_	14		ns	
Total gate charge	Qg	_	14		nC	V _{DD} = 400 V
Gate to source charge	Qgs	_	2.5		nC	V _{GS} = 10 V I _D = 6 A
Gate to drain charge	Qgd	_	6.9		nC	
Body-drain diode forward voltage	V _{DF}		0.9	1.5	V	$I_F = 6 A, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		230	—	ns	$I_F = 6 A, V_{GS} = 0$
						di _F /dt = 100 A/µs

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK5026DPE-00-J3	1000 pcs	Taping

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